NCS20081/2/4, NCV20081/2/4

1.2 MHz, 42 μA Low Power Operational Amplifier

The NCS20081/2/4 is a family of single, dual and quad Operational Amplifiers (Op Amps) with 1.2 MHz of Gain−Bandwidth Product (GBWP) and draws only 42 μA of Quiescent current. The NCS2008x has Input Offset Voltage of 4 mV and operates from 1.8 V to 5.5 V supply voltage over a wide temperature range (−40°C to +125°C). The Rail−to−Rail In/Out operation allows the designers to use the entire supply voltage range while taking advantage of the 1.2 MHz GBWP. Thus, this family offers superior performance over many industry standard parts. These devices are AEC−Q100 qualified which is denoted by the NCV suffix.

NCS2008x's low current consumption and low voltage performance in space saving packages, makes them ideal for sensor signal conditioning and low voltage current sensing applications in Automotive, Consumer and Industrial markets.

Features

- Wide Bandwidth: 1.2 MHz
- Low Supply Current/ Channel: 42 μA (typ.)
- Low Input Offset Voltage: 4 mV (max.)
- Wide Supply Range: 1.8 V to 5.5 V
- Wide Temperature Range: −40°C to +125°C
- Rail−to−Rail Input and Output
- Unity Gain Stable
- Available in Single, Dual and Quad Packages
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Automotive
- Battery Powered/ Portable Application
- Sensor Signal Conditioning
- Low Voltage Current Sensing
- Filters Circuits
- Unity Gain Buffer

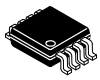
This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.

ON Semiconductor®

www.onsemi.com

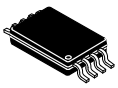
SC70−5
CASE 419A

TSOP−5/SOT23−5
CASE 483

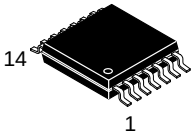


Micro8™/MSOP8
CASE 846A

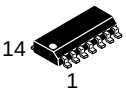
SOIC−8
CASE 751



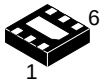
TSSOP−8
CASE 948S



TSSOP−14
CASE 948G



SOIC−14
CASE 751A



UDFN6
CASE 517AP

DEVICE MARKING INFORMATION

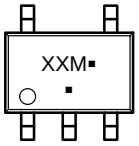
See general marking information in the device marking section on page 2 of this data sheet.

ORDERING INFORMATION

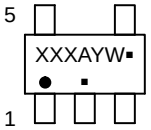
See detailed ordering and shipping information on page 3 of this data sheet.

MARKING DIAGRAMS

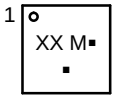
Single Channel Configuration
NCS20081, NCV20081



SC70−5
CASE 419A

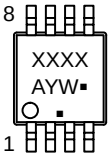


TSOP−5/SOT23−5
CASE 483

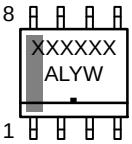


UDFN6
CASE 517AP

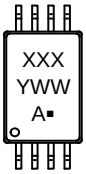
Dual Channel Configuration
NCS20082, NCV20082



Micro8™/MSOP8
CASE 846A

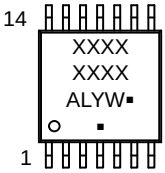


SOIC−8
CASE 751

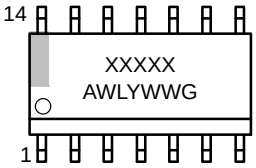


TSSOP−8
CASE 948S

Quad Channel Configuration
NCS20084, NCV20084



TSSOP−14
CASE 948G

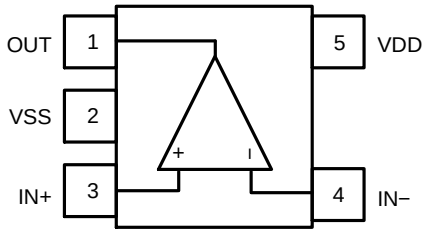


SOIC−14
CASE 751A

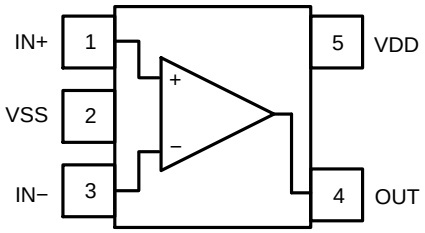
XXXXX = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or ▪ = Pb−Free Package

(Note: Microdot may be in either location)

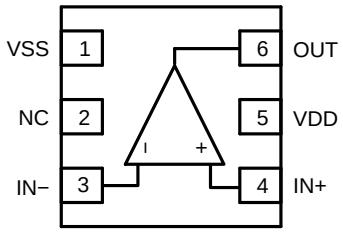
Single Channel Configuration
NCS20081, NCV20081



SOT23−5 (TSOP−5)
SN2 Pinout

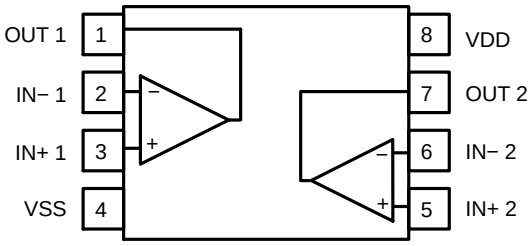


SC70−5, SOT23−5 (TSOP−5)
SQ3, SN3 Pinout



UDFN6 1.6 x 1.6

Dual Channel Configuration
NCS20082, NCV20082



Quadruple Channel Configuration
NCS20084, NCV20084

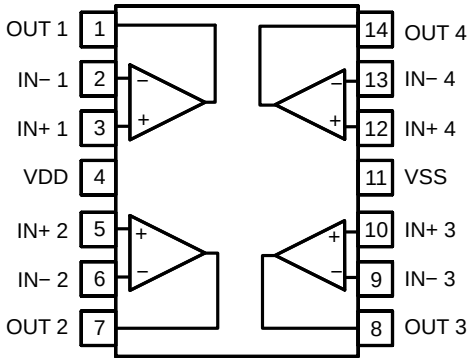


Figure 1. Pin Connections

ORDERING INFORMATION

Device	Configuration	Automotive	Marking	Package	Shipping†
NCS20081SQ3T2G	Single	No	AAP	SC70	Contact local sales office for more information
NCS20081SN2T1G			AER	SOT23−5/TSOP−5	
NCS20081SN3T1G			AEU	SOT23−5/TSOP−5	
NCS20081MUTAG			AP	UDFN6	
NCV20081SQ3T2G*		Yes	AAP	SC70	
NCV20081SN2T1G*			AER	SOT23−5/TSOP−5	
NCS20082DMR2G	Dual	No	2K82	Micro8/MSOP8	
NCS20082DR2G			NCS20082	SOIC−8	
NCS20082DTBR2G			K82	TSSOP−8	
NCV20082DMR2G*		Yes	2K82	Micro8/MSOP8	
NCV20082DR2G*			NCS20082	SOIC−8	
NCV20082DTBR2G*			K82	TSSOP−8	
NCS20084_	Quad**	No	TBD	SOIC−14	
NCS20084_			TBD	SOP−14	
NCS20084_			TBD	TSSOP−14	
NCV20084_		Yes	TBD	SOIC−14	
NCV20084_			TBD	SOP−14	
NCV20084_			TBD	TSSOP−14	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

**In Development. Not yet released.

ABSOLUTE MAXIMUM RATINGS (Note 1)

Rating		Symbol	Limit	Unit
Supply Voltage (V_{DD} – V_{SS}) (Note 2)		V_S	7	V
Input Voltage		V_I	V_{SS} − 0.5 to V_{DD} + 0.5	V
Differential Input Voltage		V_{ID}	±V_S	V
Maximum Input Current		I_I	±10	mA
Maximum Output Current		I_O	±100	mA
Continuous Total Power Dissipation (Note 2)		P_D	200	mW
Maximum Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{STG}	−65 to 150	°C
Mounting Temperature (Infrared or Convection – 20 sec)		T_{mount}	260	°C
ESD Capability (Note 3)	Human Body Model Machine Model Charge Device Model	ESD_{HBM} ESD_{MM} ESD_{CDM}	2000 100 2000	V
Latch−Up Current (Note 4)		I_{LU}	100	mA
Moisture Sensitivity Level (Note 5)		MSL	Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS for Safe Operating Area.
2. Continuous short circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of the maximum output current rating over the long term may adversely affect reliability. Shorting output to either VDD or VSS will adversely affect reliability.
3. This device series incorporates ESD protection and is tested by the following methods:
   ESD Human Body Model tested per AEC−Q100−002 (JEDEC standard: JESD22−A114)
   ESD Machine Model tested per AEC−Q100−003 (JEDEC standard: JESD22−A115)
4. Latch−up Current tested per JEDEC standard: JESD78
5. Moisture Sensitivity Level tested per IPC/JEDEC standard: J−STD−020A

THERMAL INFORMATION

Parameter	Symbol	Channels	Package	Single Layer Board (Note 6)	Multi−Layer Board (Note 7)	Unit
Junction to Ambient Thermal Resistance	θ_{JA}	Single	SC−70	491	444	°C/W
			SOT23−5/TSOP−5	310	247	
			UDFN6	278	239	
		Dual	Micro8/MSOP8	236	167	
			SOIC−8	190	131	
			TSSOP−8	253	194	
		Quad	SOIC−14			
			SOP−14			
			TSSOP−14			

6. Value based on 1S standard PCB according to JEDEC51−3 with 1.0 oz copper and a 300 mm^2 copper area
7. Value based on 1S2P standard PCB according to JEDEC51−7 with 1.0 oz copper and a 100 mm^2 copper area

OPERATING RANGES

Parameter	Symbol	Min	Max	Unit
Operating Supply Voltage	V_S	1.8	5.5	V
Differential Input Voltage	V_{ID}		V_S	V
Input Common Mode Range	V_{ICM}	V_{SS} – 0.2	V_{DD} + 0.2	V
Ambient Temperature	T_A	−40	125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS AT V_S = 1.8 V

T_A = 25°C; $R_L \geq 10$ kΩ; $V_{CM} = V_{OUT}$ = mid−supply unless otherwise noted.
Boldface limits apply over the specified temperature range, T_A = −40°C to 125°C. (Note 8)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Input Offset Voltage	V_{OS}			0.5	3.5	mV
					4	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			1		μV/°C
Input Bias Current (Note 8)	I_{IB}			1		pA
					1500	pA
Input Offset Current (Note 8)	I_{OS}			1		pA
					1100	pA
Channel Separation	XTLK	DC		125		dB
Differential Input Resistance	R_{ID}			10		GΩ
Common Mode Input Resistance	R_{IN}			10		GΩ
Differential Input Capacitance	C_{ID}			1		pF
Common Mode Input Capacitance	C_{CM}			5		pF
Common Mode Rejection Ratio	CMRR	$V_{CM} = V_{SS} - 0.2$ to $V_{DD} + 0.2$	48	73		dB
		$V_{CM} = V_{SS} + 0.2$ to $V_{DD} - 0.2$	**45**			
OUTPUT CHARACTERISTICS						
Open Loop Voltage Gain	A_{VOL}		86	120		dB
			80			
Short Circuit Current	I_{SC}	Output to positive rail, sinking current		15		mA
		Output to negative rail, sourcing current		11		
Output Voltage High	V_{OH}	Voltage output swing from positive rail		3	19	mV
					20	
Output Voltage Low	V_{OL}	Voltage output swing from negative rail		3	19	mV
					20	
AC CHARACTERISTICS						
Unity Gain Bandwidth	UGBW			1.2		MHz
Slew Rate at Unity Gain	SR	V_{ID} = 1.2 Vpp, Gain = 1		0.4		V/μs
Phase Margin	ψ_m			60		°
Gain Margin	A_m			19		dB
Settling Time	t_S	V_{IN} = 1.2 Vpp, Gain = 1; Settling time to 0.1%		5		μs
		V_{IN} = 1.2 Vpp, Gain = 1; Settling time to 0.01%		6		
Open Loop Output Impedance	Z_{OL}	f = 100 Hz		0.8		Ω
NOISE CHARACTERISTICS						
Total Harmonic Distortion plus Noise	THD+N	V_{IN} = 1.2 Vpp, f = 1 kHz, Av = 1		0.005		%
Input Referred Voltage Noise	e_n	f = 1 kHz		30		nV/√Hz
		f = 10 kHz		24		
Input Referred Current Noise	i_n	f = 1 kHz		300		fA/√Hz
SUPPLY CHARACTERISTICS						
Power Supply Rejection Ratio	PSRR	No Load	67	90		dB
			64			
Power Supply Quiescent Current	I_{DD}	Per channel, no load		42	**60**	μA

8. Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT V_S = 3.3 V

T_A = 25°C; $R_L \geq 10$ kΩ; $V_{CM} = V_{OUT}$ = mid−supply unless otherwise noted.
Boldface limits apply over the specified temperature range, T_A = −40°C to 125°C. (Note 9)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Input Offset Voltage	V_{OS}			0.5	3.5	mV
					4	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			1		μV/°C
Input Bias Current (Note 9)	I_{IB}			1		pA
					1500	pA
Input Offset Current (Note 9)	I_{OS}			1		pA
					1100	pA
Channel Separation	XTLK	DC		125		dB
Differential Input Resistance	R_{ID}			10		GΩ
Common Mode Input Resistance	R_{IN}			10		GΩ
Differential Input Capacitance	C_{ID}			1		pF
Common Mode Input Capacitance	C_{CM}			5		pF
Common Mode Rejection Ratio	CMRR	$V_{CM} = V_{SS} - 0.2$ to $V_{DD} + 0.2$	53	76		dB
		$V_{CM} = V_{SS} + 0.2$ to $V_{DD} - 0.2$	**48**			
OUTPUT CHARACTERISTICS						
Open Loop Voltage Gain	A_{VOL}		90	120		dB
			86			
Short Circuit Current	I_{SC}	Output to positive rail, sinking current		15		mA
		Output to negative rail, sourcing current		11		
Output Voltage High	V_{OH}	Voltage output swing from positive rail		3	24	mV
					25	
Output Voltage Low	V_{OL}	Voltage output swing from negative rail		3	24	mV
					25	
AC CHARACTERISTICS						
Unity Gain Bandwidth	UGBW			1.2		MHz
Slew Rate at Unity Gain	SR	V_{IN} = 2.5 Vpp, Gain = 1		0.4		V/μs
Phase Margin	ψ_m			60		°
Gain Margin	A_m			18		dB
Settling Time	t_S	V_{IN} = 2.5 Vpp, Gain = 1; Settling time to 0.1%		5		μs
		V_{IN} = 2.5 Vpp, Gain = 1; Settling time to 0.01%		6		
Open Loop Output Impedance	Z_{OL}	f = 100 Hz		0.8		Ω
NOISE CHARACTERISTICS						
Total Harmonic Distortion plus Noise	THD+N	V_{IN} = 2.5 Vpp, f = 1 kHz, Av = 1		0.005		%
Input Referred Voltage Noise	e_n	f = 1 kHz		30		nV/√Hz
		f = 10 kHz		24		
Input Referred Current Noise	i_n	f = 1 kHz		300		fA/√Hz
SUPPLY CHARACTERISTICS						
Power Supply Rejection Ratio	PSRR	No Load	67	90		dB
			64			
Power Supply Quiescent Current	I_{DD}	Per channel, no load		42	**60**	μA

9. Performance guaranteed over the indicated operating temperature range by design and/or characterization.

ELECTRICAL CHARACTERISTICS AT V_S = 5.5 V

T_A = 25°C; $R_L \geq 10$ kΩ; $V_{CM} = V_{OUT}$ = mid−supply unless otherwise noted.
Boldface limits apply over the specified temperature range, T_A = −40°C to 125°C. (Note 10)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Input Offset Voltage	V_{OS}			0.5	3.5	mV
					4	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			1		μV/°C
Input Bias Current (Note 10)	I_{IB}			1		pA
					1500	pA
Input Offset Current (Note 10)	I_{OS}			1		pA
					1100	pA
Channel Separation	XTLK	DC		125		dB
Differential Input Resistance	R_{ID}			10		GΩ
Common Mode Input Resistance	R_{IN}			10		GΩ
Differential Input Capacitance	C_{ID}			1		pF
Common Mode Input Capacitance	C_{CM}			5		pF
Common Mode Rejection Ratio	CMRR	$V_{CM} = V_{SS} - 0.2$ to $V_{DD} + 0.2$	55	79		dB
		$V_{CM} = V_{SS} + 0.2$ to $V_{DD} - 0.2$	**51**			
OUTPUT CHARACTERISTICS						
Open Loop Voltage Gain	A_{VOL}		90	120		dB
			86			
Short Circuit Current	I_{SC}	Output to positive rail, sinking current		15		mA
		Output to negative rail, sourcing current		11		
Output Voltage High	V_{OH}	Voltage output swing from positive rail		3	24	mV
					25	
Output Voltage Low	V_{OL}	Voltage output swing from negative rail		3	24	mV
					25	
AC CHARACTERISTICS						
Unity Gain Bandwidth	UGBW			1.2		MHz
Slew Rate at Unity Gain	SR	V_{ID} = 5 Vpp, Gain = 1		0.4		V/μs
Phase Margin	ψ_m			60		°
Gain Margin	A_m			17		dB
Settling Time	t_S	V_{IN} = 5 Vpp, Gain = 1; Settling time to 0.1%		5		μs
		V_{IN} = 5 Vpp, Gain = 1; Settling time to 0.01%		6		
Open Loop Output Impedance	Z_{OL}	f = 100 Hz		0.8		Ω
NOISE CHARACTERISTICS						
Total Harmonic Distortion plus Noise	THD+N	V_{IN} = 5 Vpp, f = 1 kHz, Av = 1		0.005		%
Input Referred Voltage Noise	e_n	f = 1 kHz		30		nV/√Hz
		f = 10 kHz		24		
Input Referred Current Noise	i_n	f = 1 kHz		300		fA/√Hz
SUPPLY CHARACTERISTICS						
Power Supply Rejection Ratio	PSRR	No Load	67	90		dB
			64			
Power Supply Quiescent Current	I_{DD}	Per channel, no load		48	**70**	μA

10. Performance guaranteed over the indicated operating temperature range by design and/or characterization.
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

T_A = 25°C, R_L ≥ 10 kΩ, V_{CM} = V_{OUT} = mid−supply unless otherwise specified

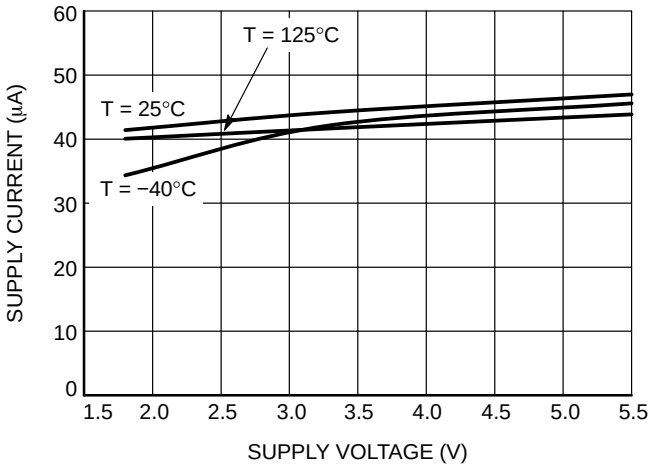


Figure 2. Quiescent Current per Channel vs. Supply Voltage

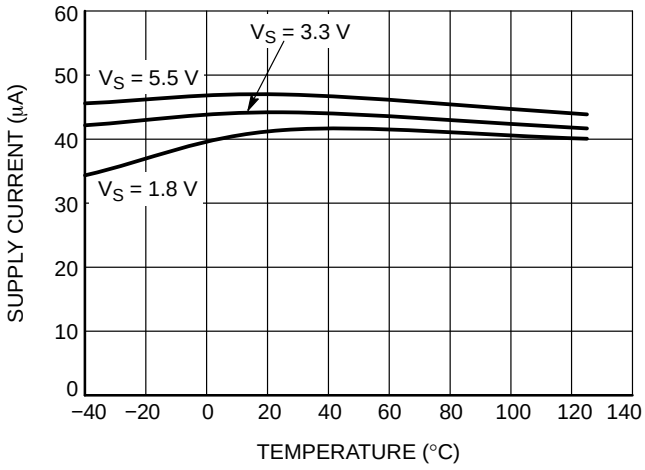


Figure 3. Quiescent Current vs. Temperature

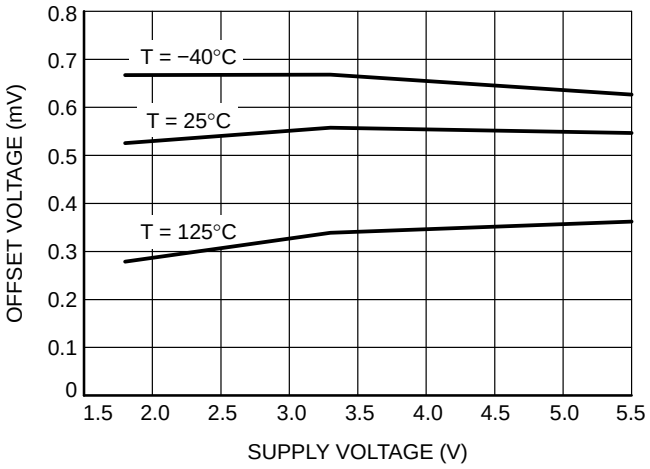


Figure 4. Offset Voltage vs. Supply Voltage

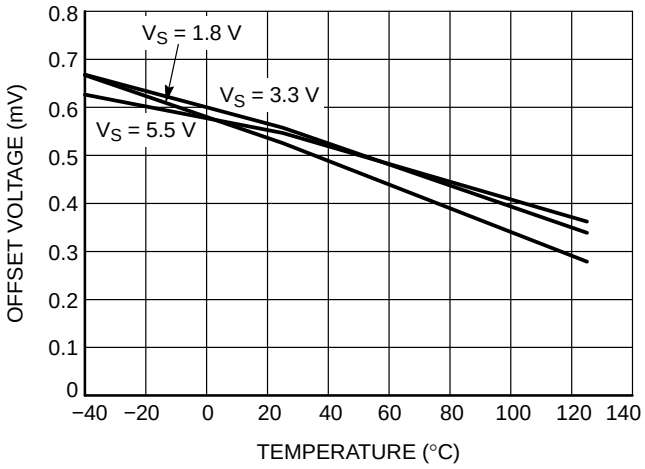


Figure 5. Offset Voltage vs. Temperature

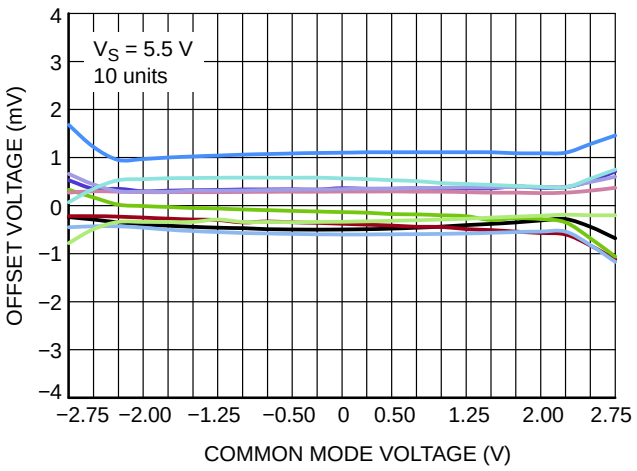


Figure 6. Offset Voltage vs. Common Mode Voltage

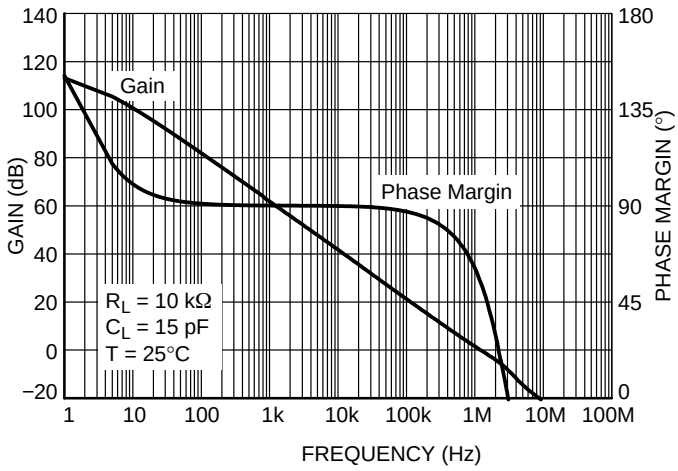


Figure 7. Open−loop Gain and Phase Margin vs. Frequency

TYPICAL PERFORMANCE CHARACTERISTICS

T_A = 25°C, R_L ≥ 10 kΩ, V_{CM} = V_{OUT} = mid−supply unless otherwise specified

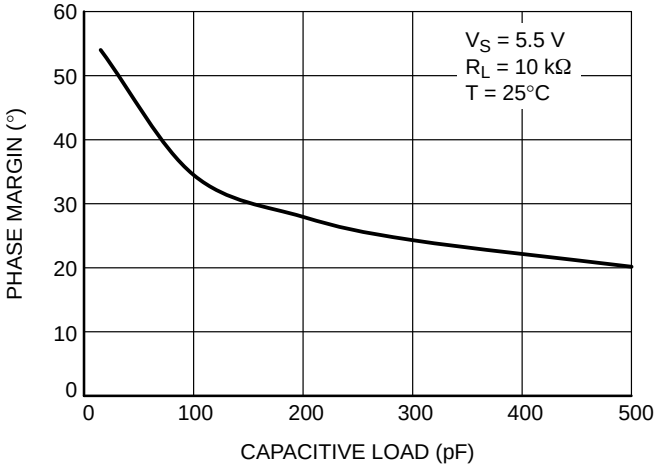


Figure 8. Phase Margin vs. Capacitive Load

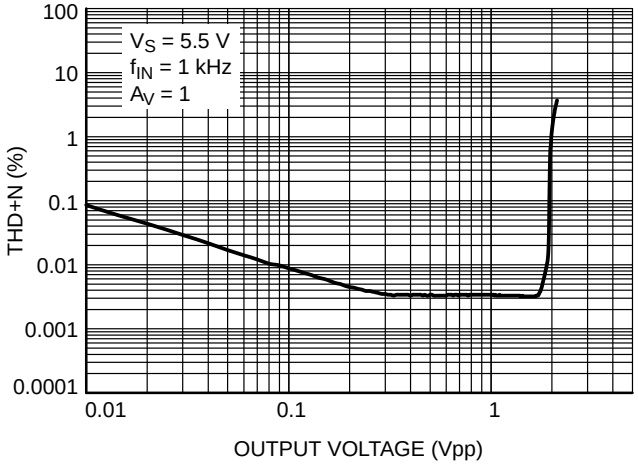


Figure 9. THD + N vs. Output Voltage

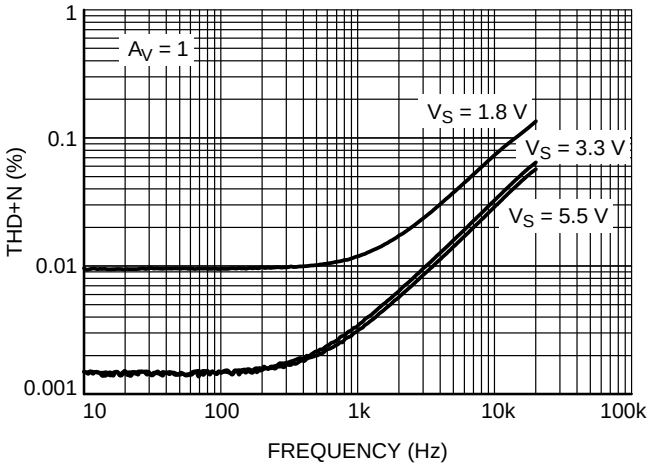


Figure 10. THD + N vs. Frequency

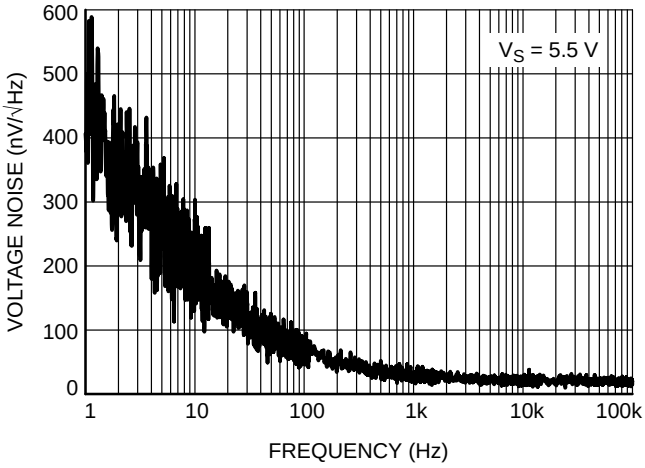


Figure 11. Input Voltage Noise vs. Frequency

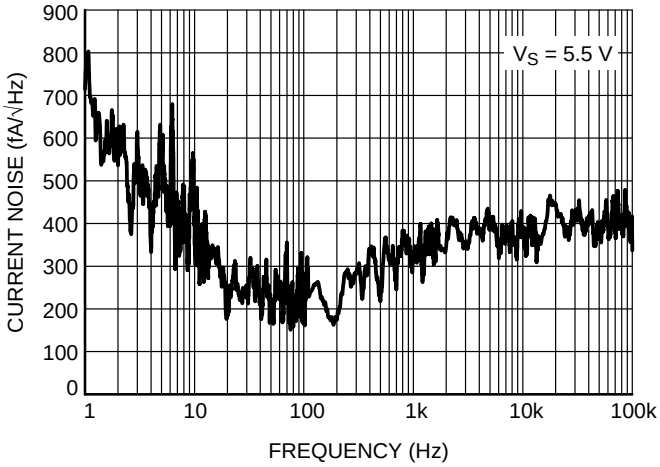


Figure 12. Input Current Noise vs. Frequency

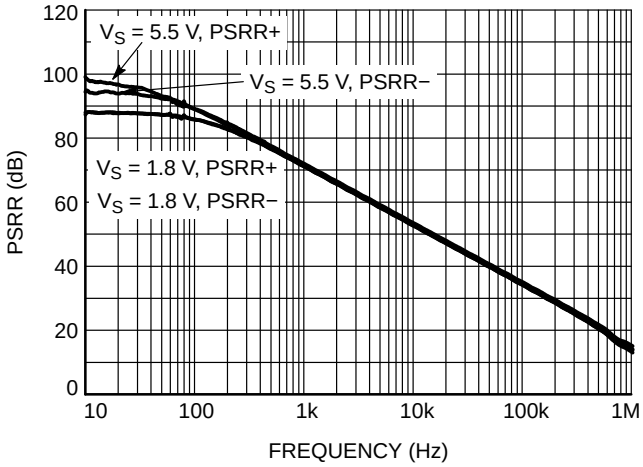


Figure 13. PSRR vs. Frequency

TYPICAL PERFORMANCE CHARACTERISTICS

T_A = 25°C, R_L ≥ 10 kΩ, V_{CM} = V_{OUT} = mid−supply unless otherwise specified

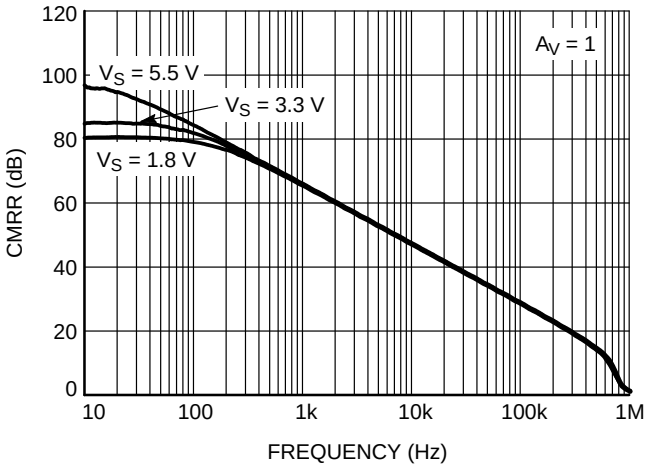


Figure 14. CMRR vs. Frequency

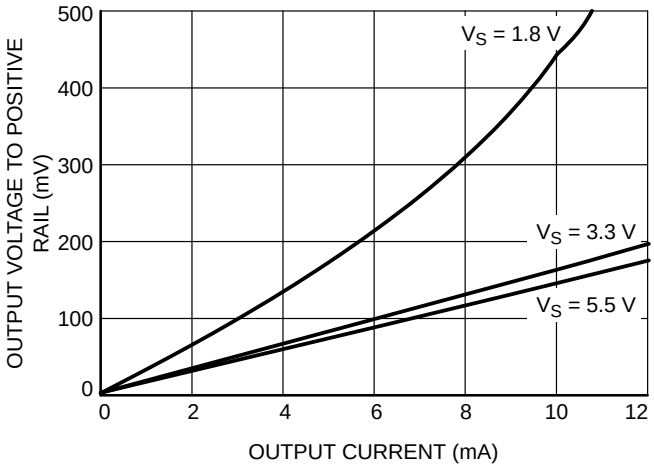


Figure 15. Output Voltage High to Rail

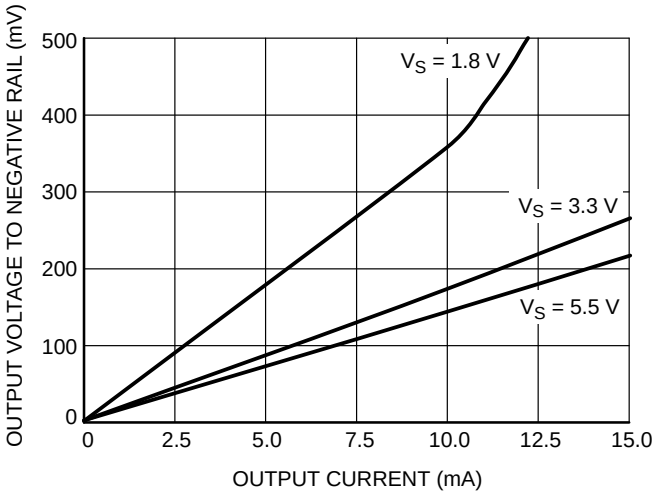


Figure 16. Output Voltage Low to Rail

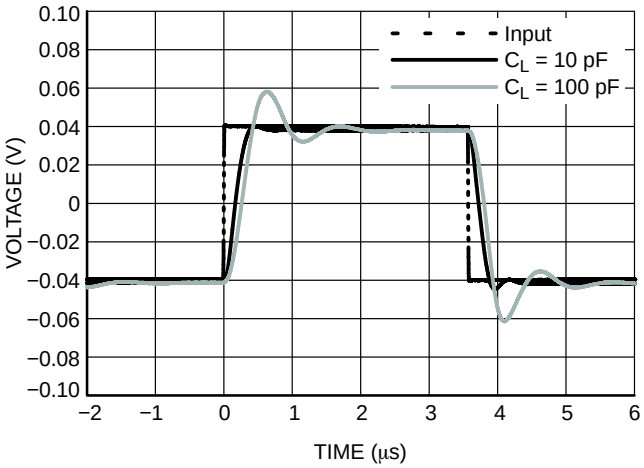


Figure 17. Non−Inverting Small Signal Transient Response

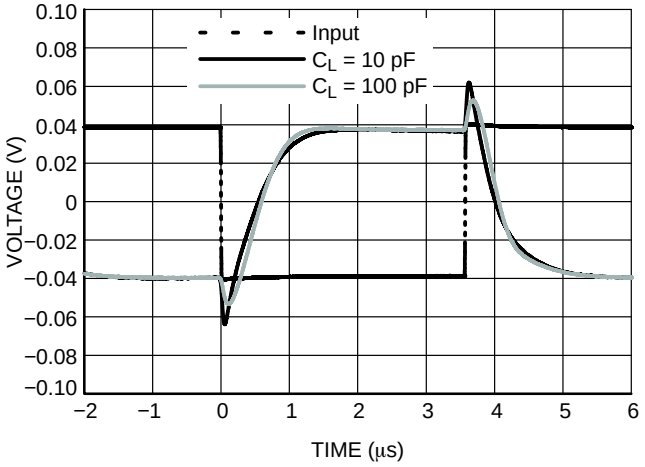


Figure 18. Inverting Small Signal Transient Response

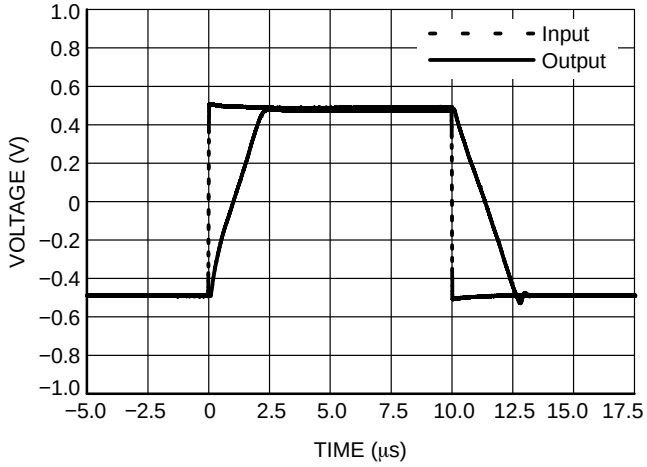


Figure 19. Non−Inverting Large Signal Transient Response

TYPICAL PERFORMANCE CHARACTERISTICS

T_A = 25°C, R_L ≥ 10 kΩ, V_{CM} = V_{OUT} = mid−supply unless otherwise specified

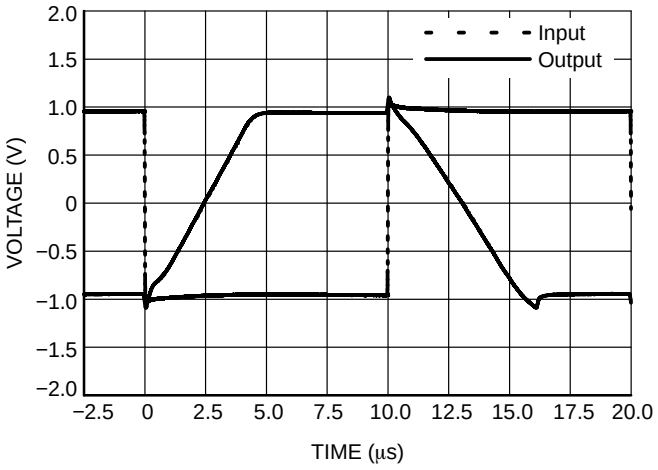


Figure 20. Inverting Large Signal Transient Response

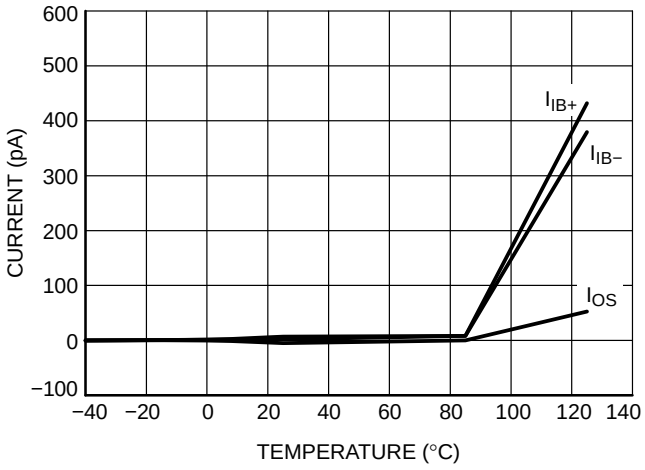


Figure 21. Input Bias and Offset Current vs. Temperature

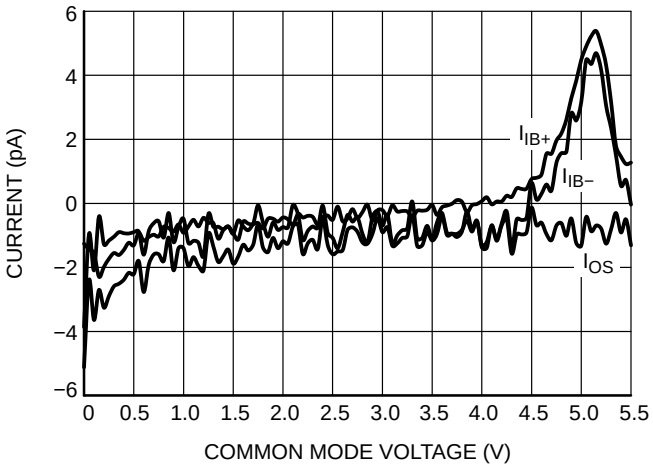


Figure 22. Input Bias Current vs. Common Mode Voltage

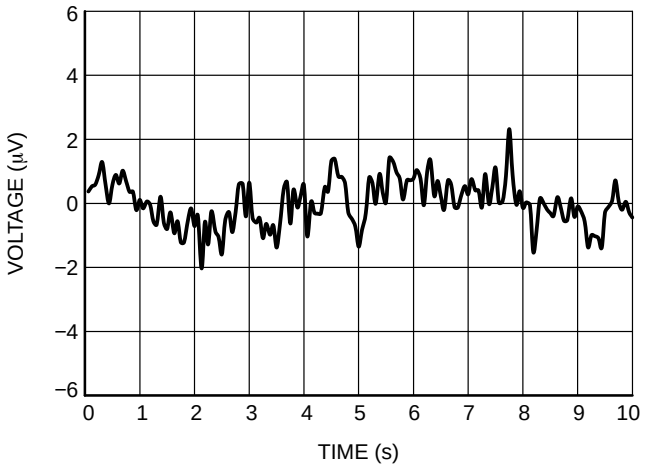


Figure 23. 0.1 Hz to 10 Hz Noise

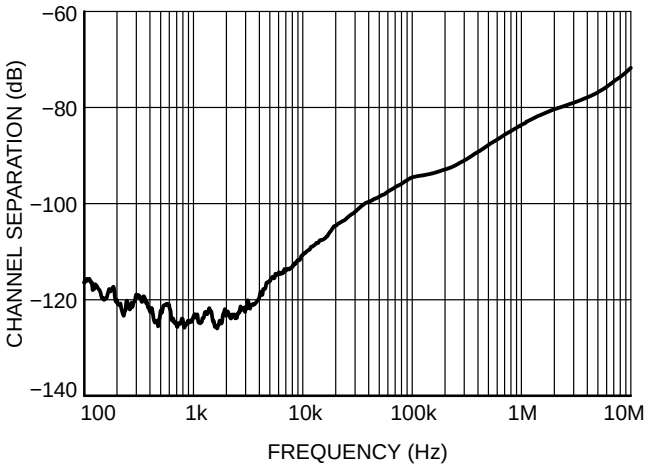


Figure 24. Channel Separation vs. Frequency

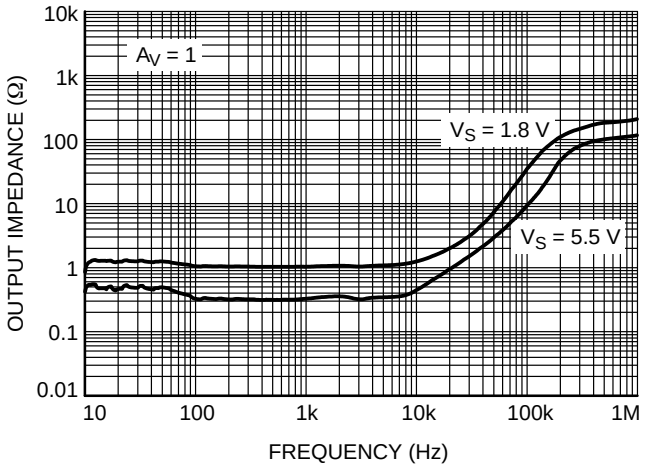


Figure 25. Output Impedance vs. Frequency

TYPICAL PERFORMANCE CHARACTERISTICS

T_A = 25°C, $R_L \geq 10$ kΩ, $V_{CM} = V_{OUT}$ = mid−supply unless otherwise specified

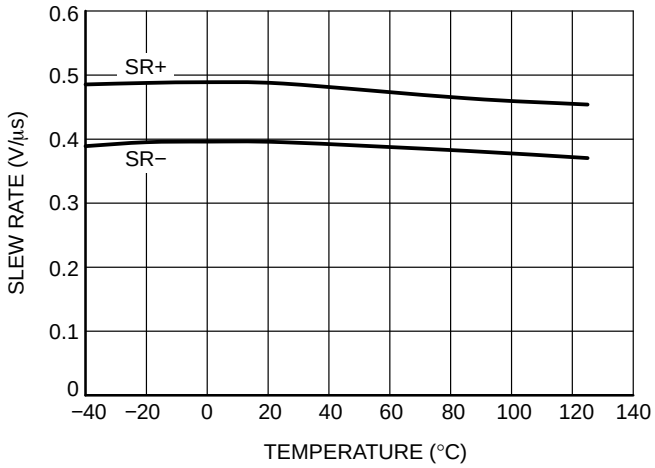
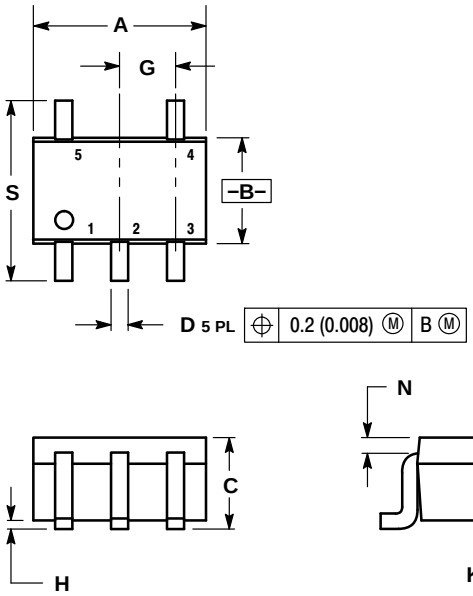


Figure 26. Slew Rate vs. Temperature

PACKAGE DIMENSIONS

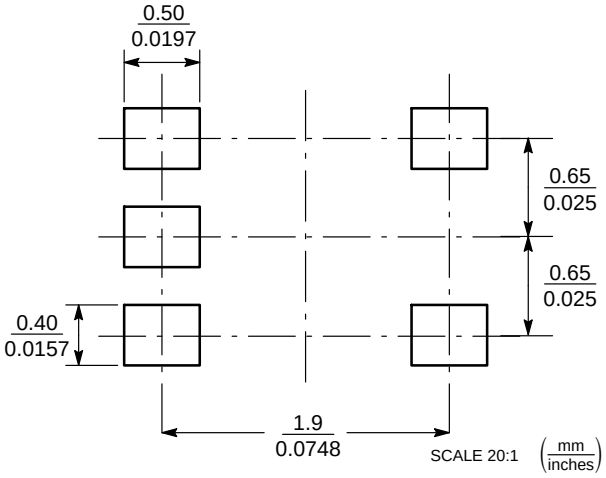
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE L



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

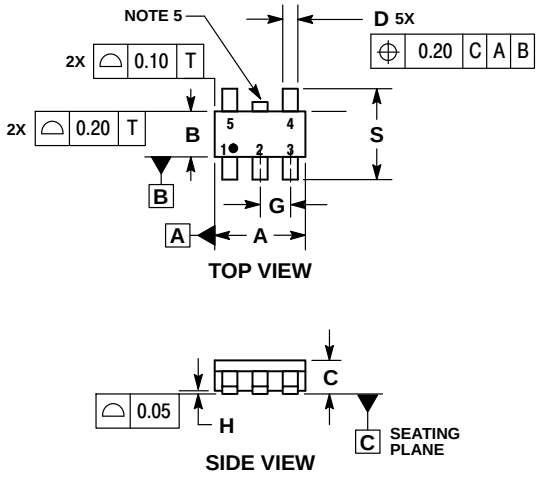
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

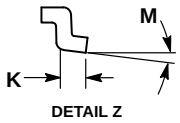
SOLDER FOOTPRINT

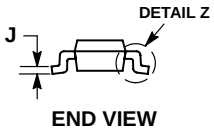


PACKAGE DIMENSIONS

TSOP−5
CASE 483
ISSUE L



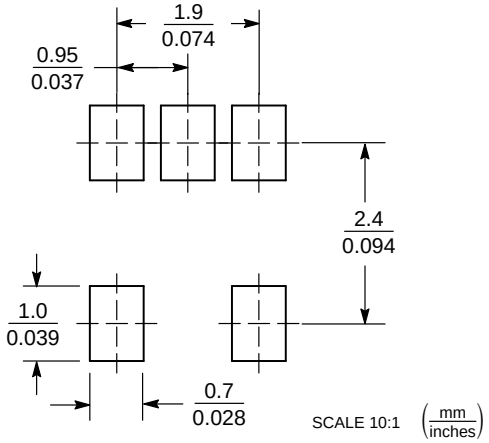




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS	
DIM	MIN	MAX
A	3.00 BSC	
B	1.50 BSC	
C	0.90	1.10
D	0.25	0.50
G	0.95 BSC	
H	0.01	0.10
J	0.10	0.26
K	0.20	0.60
M	0 °	10 °
S	2.50	3.00

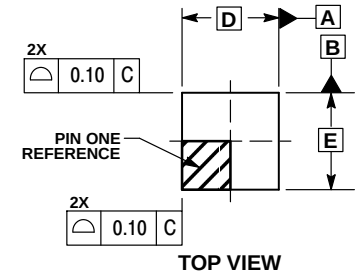
SOLDERING FOOTPRINT*



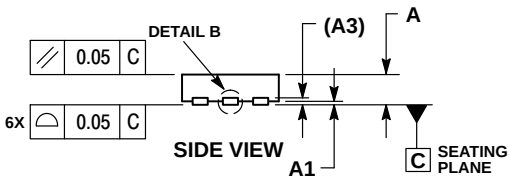
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

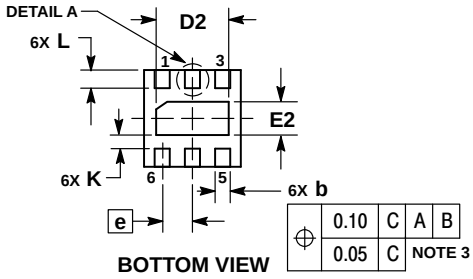
PACKAGE DIMENSIONS

UDFN6 1.6x1.6, 0.5P
CASE 517AP
ISSUE O

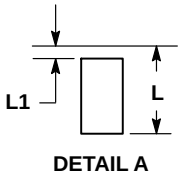


TOP VIEW

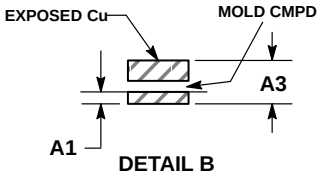




BOTTOM VIEW



DETAIL A
OPTIONAL CONSTRUCTION

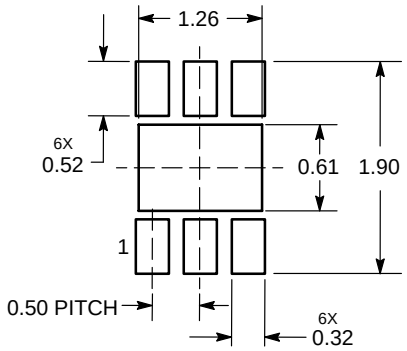


DETAIL B
OPTIONAL CONSTRUCTION

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.20	0.30
D	1.60 BSC	
E	1.60 BSC	
e	0.50 BSC	
D2	1.10	1.30
E2	0.45	0.65
K	0.20	---
L	0.20	0.40
L1	0.00	0.15

SOLDERMASK DEFINED MOUNTING FOOTPRINT*

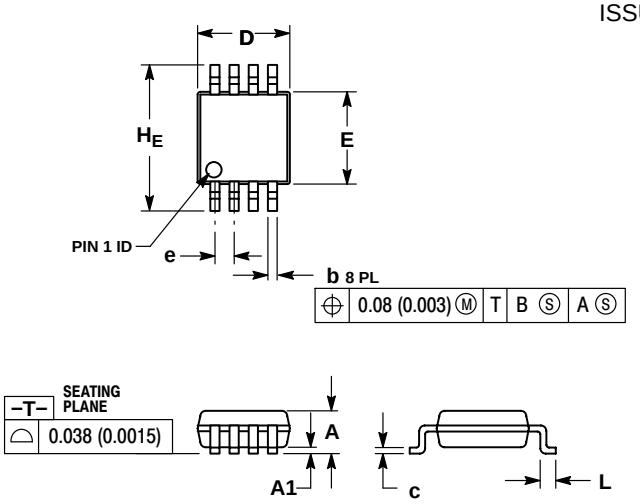


DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

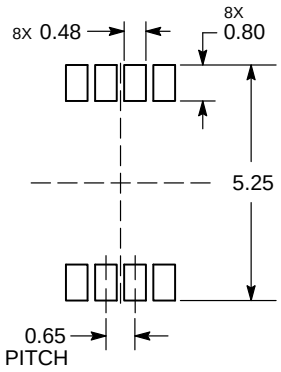
Micro8™
CASE 846A−02
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. 846A−01 OBSOLETE, NEW STANDARD 846A−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	−−	−−	1.10	−−	−−	0.043
A1	0.05	0.08	0.15	0.002	0.003	0.006
b	0.25	0.33	0.40	0.010	0.013	0.016
c	0.13	0.18	0.23	0.005	0.007	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
E	2.90	3.00	3.10	0.114	0.118	0.122
e	0.65 BSC			0.026 BSC		
L	0.40	0.55	0.70	0.016	0.021	0.028
H_E	4.75	4.90	5.05	0.187	0.193	0.199

RECOMMENDED SOLDERING FOOTPRINT*

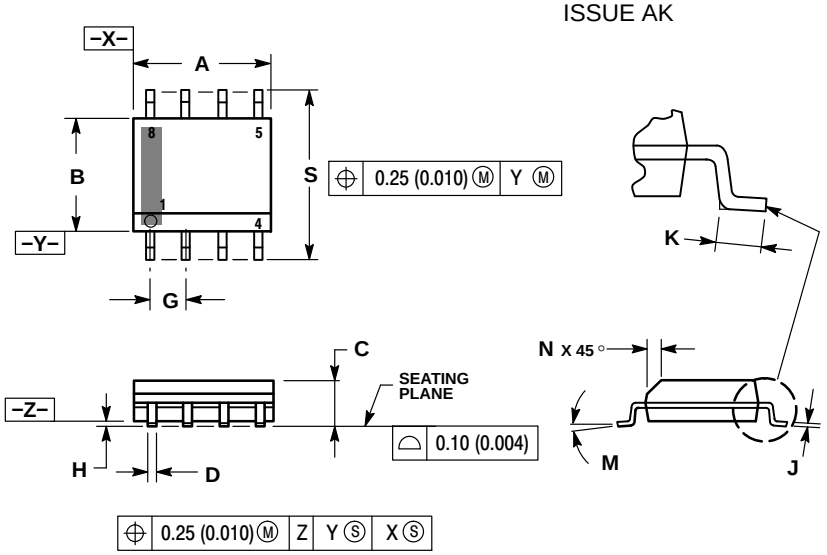


DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC−8 NB
CASE 751−07
ISSUE AK

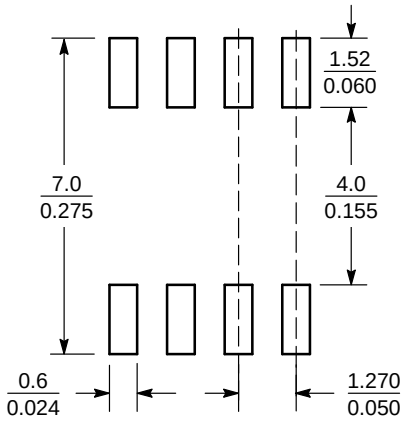


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

SOLDERING FOOTPRINT*

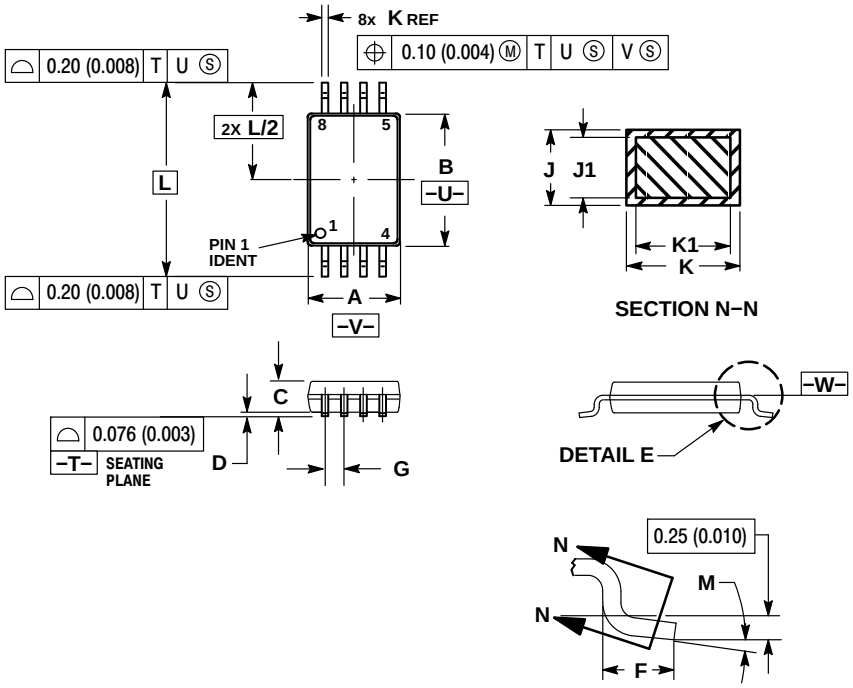


SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP−8
CASE 948S
ISSUE C



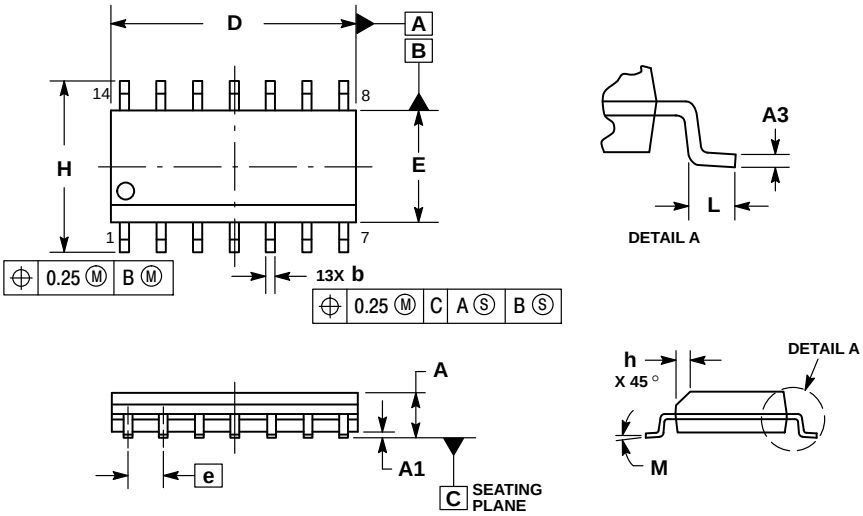
DETAIL E

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	4.30	4.50	0.169	0.177
C	---	1.10	---	0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

PACKAGE DIMENSIONS

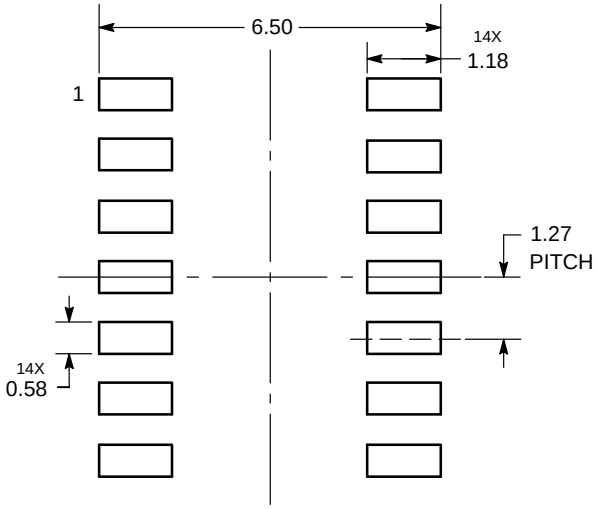
SOIC−14 NB
CASE 751A−03
ISSUE K



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

SOLDERING FOOTPRINT*

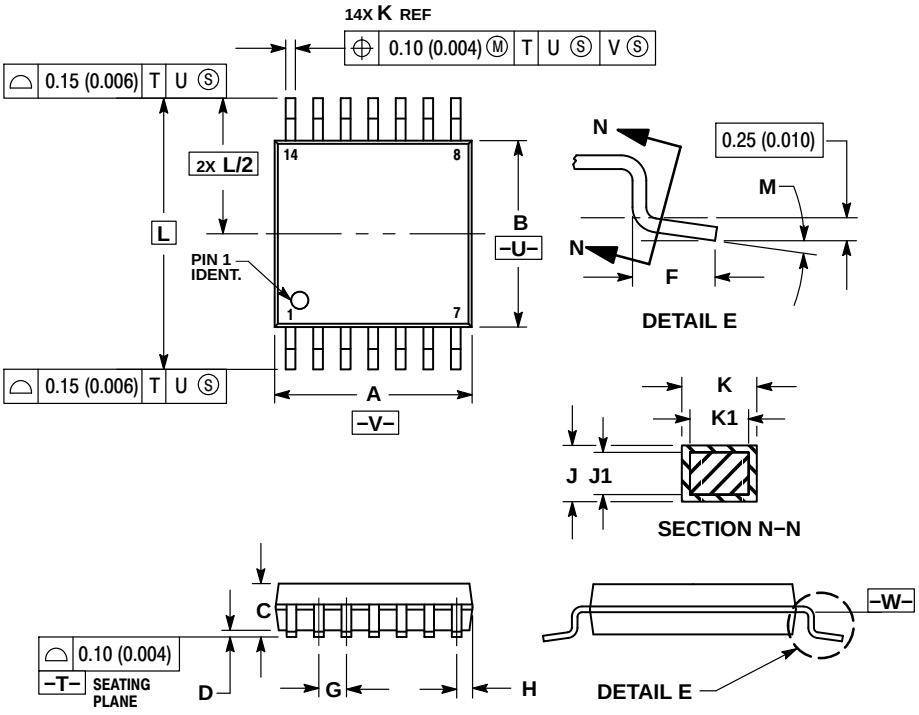


DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

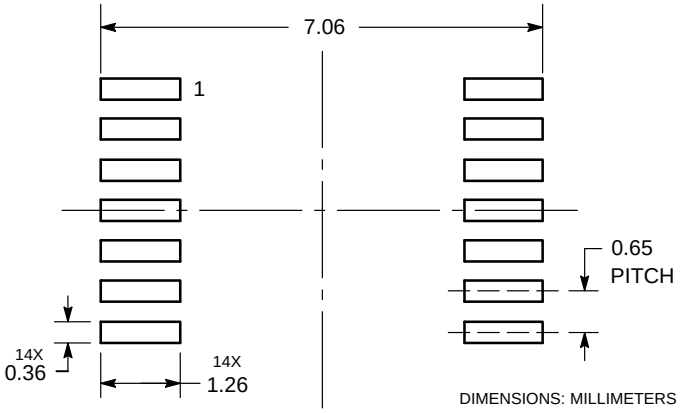
TSSOP−14
CASE 948G
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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